

P-Channel Power MOSFET

-30V, -34A, 8.5mΩ

FEATURES

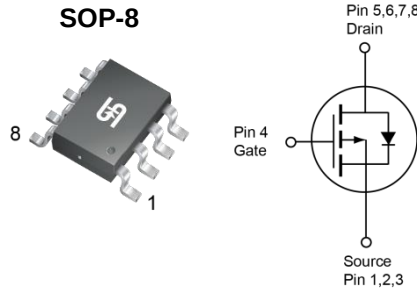
- Low $R_{DS(ON)}$ to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- DC-DC Converters
- Battery Power Management
- Load Switch
- BLDC Motor Drives

KEY PERFORMANCE PARAMETERS

PARAMETER	VALUE	UNIT
V_{DS}	-30	V
$R_{DS(on)}$ (max)	$V_{GS} = -10V$	8.5
	$V_{GS} = -4.5V$	14
Q_g	28	nC



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	$T_C = 25^\circ\text{C}$	A
		$T_A = 25^\circ\text{C}$	
Pulsed Drain Current	I_{DM}	-136	A
Single Pulse Avalanche Current (Note 2)	I_{AS}	-23	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	79	mJ
Total Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 125^\circ\text{C}$	
Total Power Dissipation	P_D	$T_A = 25^\circ\text{C}$	W
		$T_A = 125^\circ\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	9	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	57	$^\circ\text{C/W}$

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = -250μA	BV _{DSS}	-30	--	--	V
Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = -250μA	V _{GS(TH)}	-1.2	-1.5	-2.5	V
Gate-Source Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Drain-Source Leakage Current	V _{GS} = 0V, V _{DS} = -30V	I _{DSS}	--	--	-1	μA
	V _{GS} = 0V, V _{DS} = -30V T _J = 125°C		--	--	-100	
	Drain-Source On-State Resistance (Note 3)		V _{GS} = -10V, I _D = -13A	R _{DS(on)}	--	
	V _{GS} = -4.5V, I _D = -10A	--	11		14	
Forward Transconductance (Note 3)	V _{DS} = -5V, I _D = -13A	g _{fs}	--	35	--	S
Dynamic (Note 4)						
Total Gate Charge	V _{GS} = -10V, V _{DS} = -15V, I _D = -13A	Q _g	--	56	--	nC
Total Gate Charge	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -10A	Q _g	--	28	--	
Gate-Source Charge		Q _{gs}	--	9	--	
Gate-Drain Charge		Q _{gd}	--	11	--	
Input Capacitance	V _{GS} = 0V, V _{DS} = -15V f = 1.0MHz	C _{iss}	--	3216	--	pF
Output Capacitance		C _{oss}	--	409	--	
Reverse Transfer Capacitance		C _{rss}	--	277	--	
Gate Resistance	f = 1.0MHz	R _g	1.8	6	12	Ω
Switching (Note 4)						
Turn-On Delay Time	V _{GS} = -10V, V _{DS} = -15V, I _D = -13A, R _G = 2Ω	t _{d(on)}	--	7.2	--	ns
Turn-On Rise Time		t _r	--	2.6	--	
Turn-Off Delay Time		t _{d(off)}	--	68	--	
Turn-Off Fall Time		t _f	--	33	--	
Source-Drain Diode						
Forward Voltage (Note 3)	V _{GS} = 0V, I _S = -13A	V _{SD}	--	--	-1	V
Reverse Recovery Time	I _S = -13A , di/dt = 100A/μs	t _{rr}	--	34	--	ns
Reverse Recovery Charge		Q _{rr}	--	19	--	nC

Notes:

- Silicon limited current only.
- $L = 0.3\text{mH}$, $V_{GS} = -10V$, $V_{DD} = -25V$, $R_G = 25\Omega$, $I_{AS} = -23A$, Starting $T_J = 25^\circ\text{C}$
- Pulse test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.

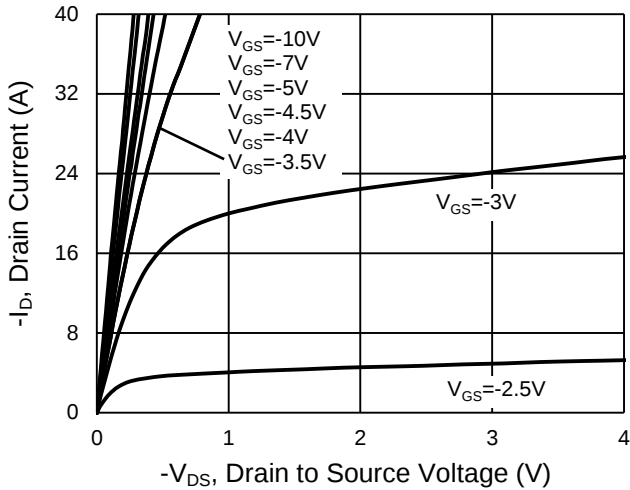
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM085P03CS RLG	SOP-8	2,500pcs / 13" Reel

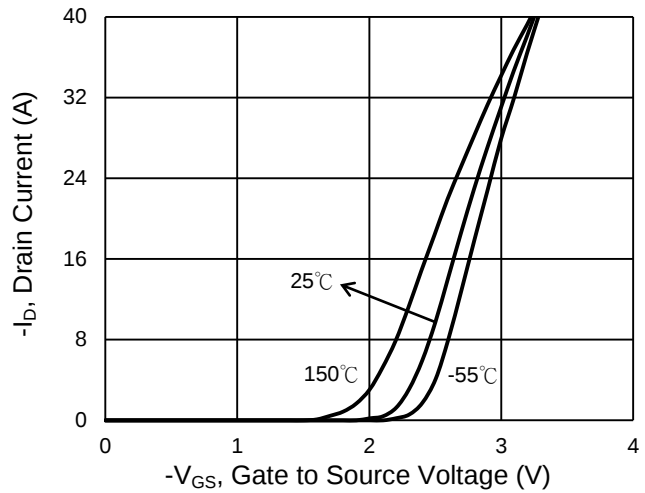
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

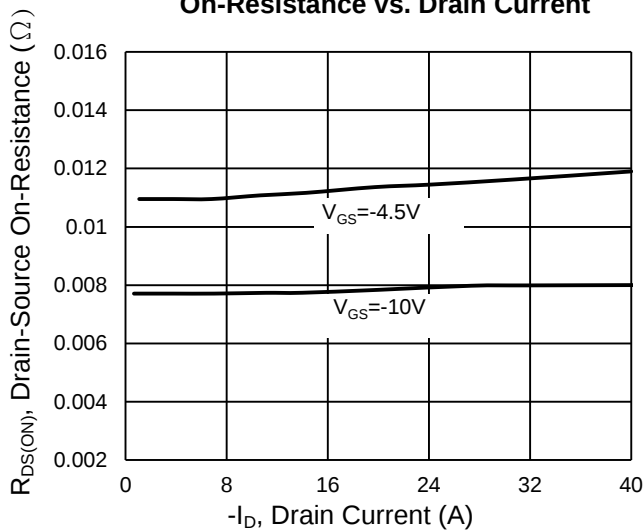
Output Characteristics



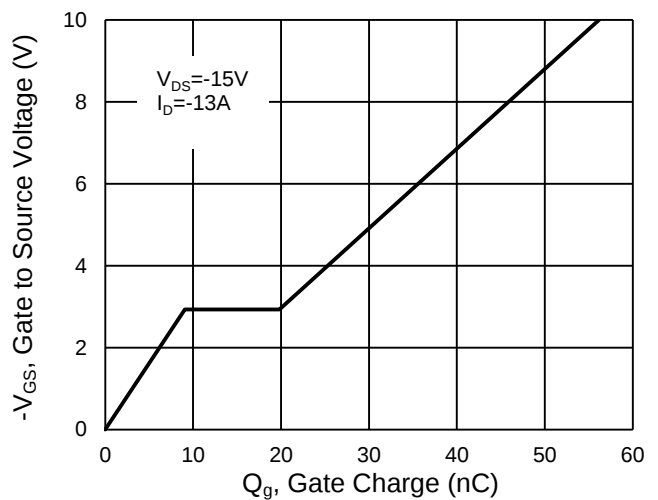
Transfer Characteristics



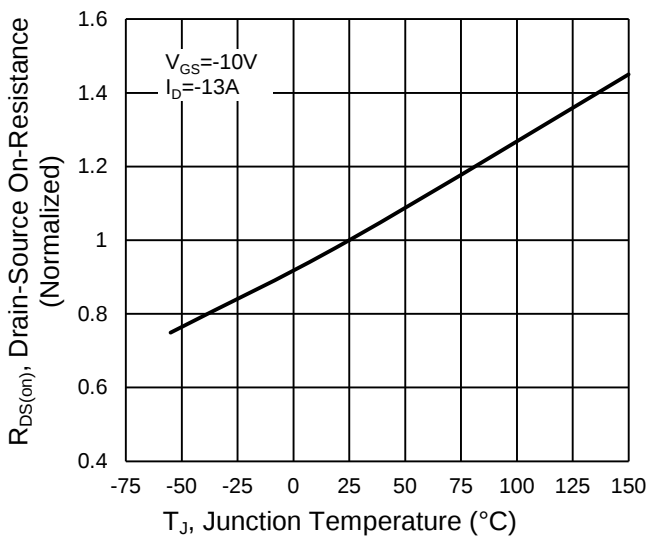
On-Resistance vs. Drain Current



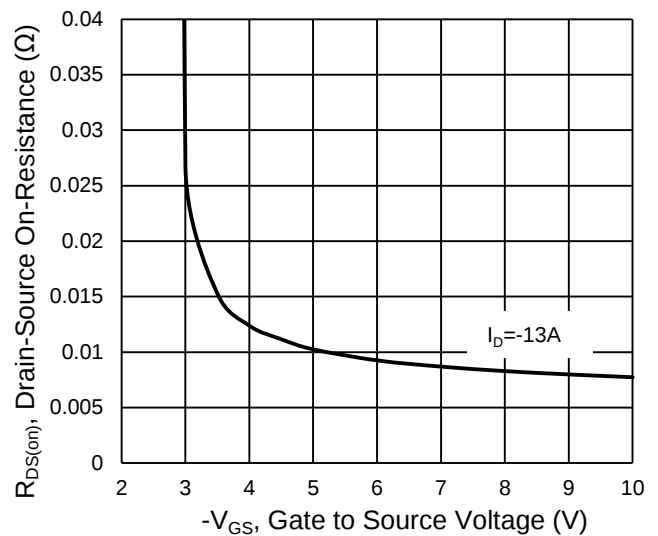
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



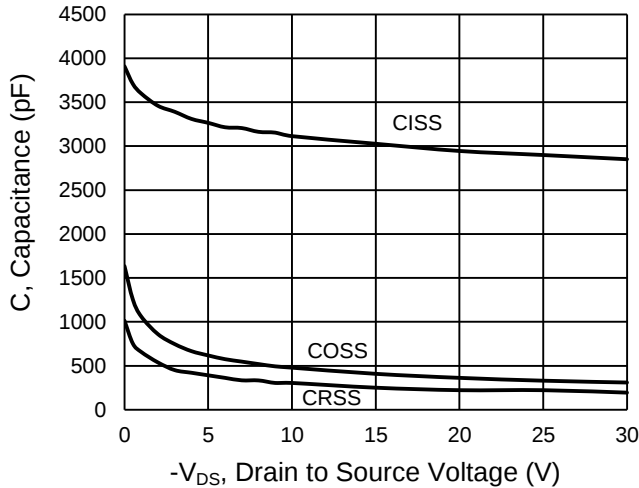
On-Resistance vs. Gate-Source Voltage



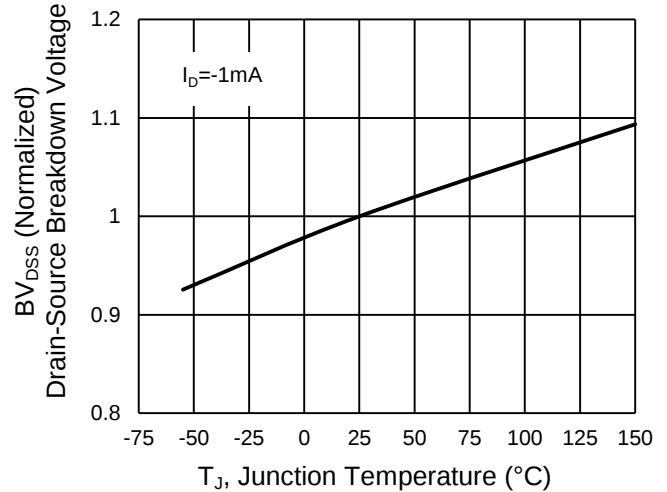
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

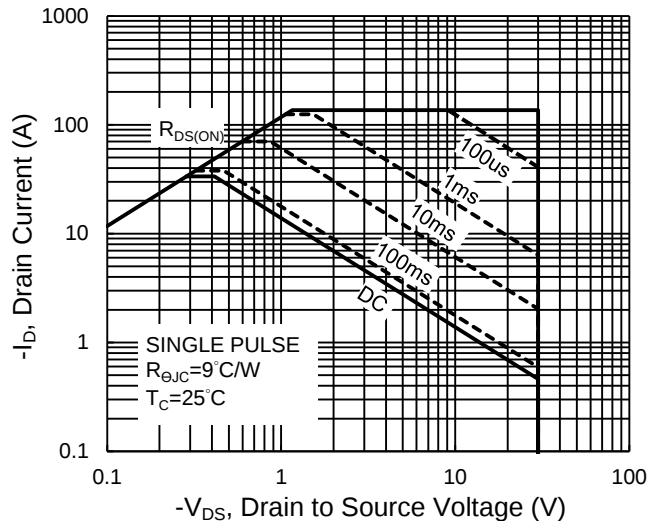
Capacitance vs. Drain-Source Voltage



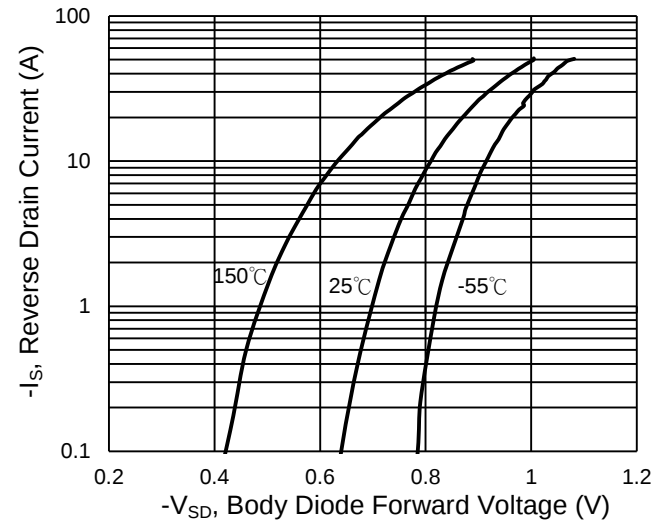
BV_{DSS} vs. Junction Temperature



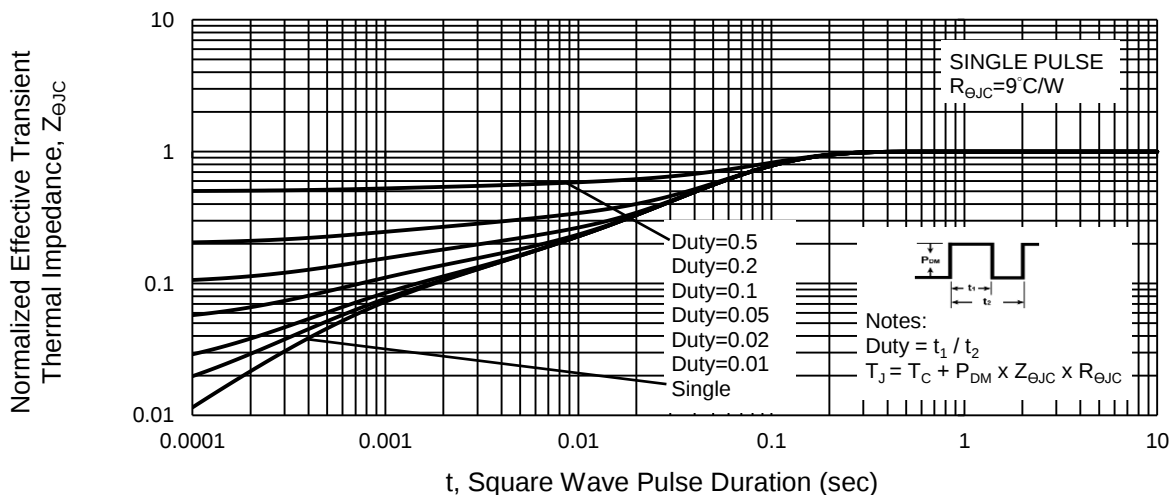
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

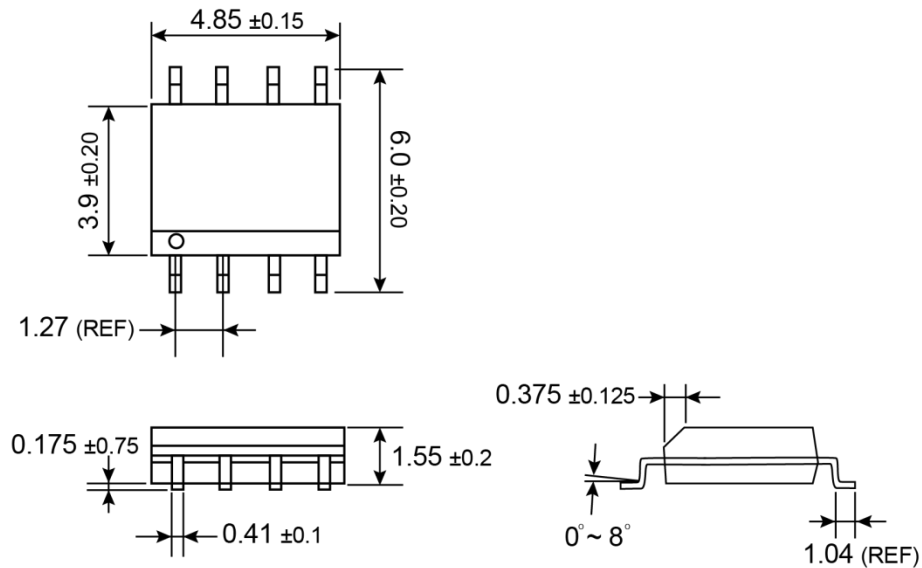


Normalized Thermal Transient Impedance, Junction-to-Case

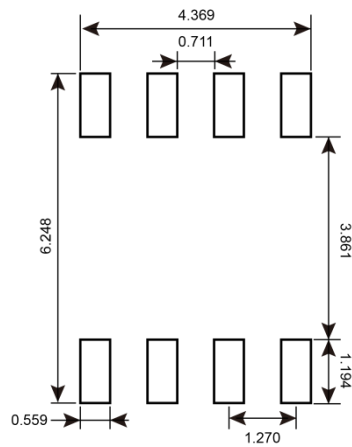


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

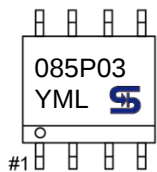
SOP-8



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code

O =Jan

P =Feb

Q =Mar

R =Apr

S =May

T =Jun

U =Jul

V =Aug

W =Sep

X =Oct

Y =Nov

Z =Dec

L = Lot Code (1~9, A~Z)

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